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IAP11 Rec'd PCT/PTO 07 AUG 2006

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

SUGAWARA

Atty. Ref.: 925-348

Serial No. Unknown

TC/A.U.: Unknown

Filed: August 7, 2006

Examiner: Unknown

For: HIGH-WITHSTAND VOLTAGE WIDE-GAP SEMICONDUCTOR DEVICE
AND POWER DEVICE

* * * * *

August 7, 2006

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO/SB/08a. A copy of each listed foreign patent document and article is attached.

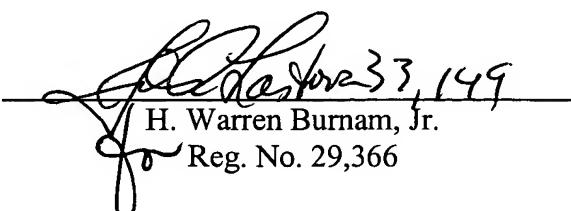
This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO/SB/08a and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

Respectfully submitted,

NIXON & VANDERHYE P.C.

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INFORMATION DISCLOSURE CITATION	ATTY. DOCKET NO.	SERIAL NO.
	925-348	Unknown
	APPLICANT	
	SUGAWARA	
(Use several sheets if necessary)	FILING DATE	TC/A.U.
	August 7, 2006	Unknown

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

	International Search Report for PCT/JP2005/001705 dated 10 May 2005.
	Matsunami, <i>Semiconductor SiC Technology and Applications</i> , High-Withstand Voltage FET, Nikkan Kogyo Shimbunsha, March 31, 2003, pp. 218-221.
	Agarwal et al., <i>Dynamic Performance of 3.1 kV 4H-SiC Asymmetrical GTO Thyristors</i> , Materials Science Forum, vols. 389-393, 2002, pp. 1349-1352.
	Chatty et al., <i>Comparison of Nitrogen and Phosphorus Implanted, Planar, High-Voltage 4H-SiC Junction Rectifiers</i> , Materials Science Forum, vols. 338-342, 2000, pp. 1331-1334.

*Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.